74LVC16245A-Q100; 74LVCH16245A-Q100

16-bit bus transceiver with direction pin; 5 V tolerant; 3-state

Rev. 1 — 20 November 2012 Product data sheet

1. General description

The 74LVC16245A-Q100; 74LVCH16245A-Q100 are 16-bit transceivers featuring non-inverting 3-state bus compatible outputs in both send and receive directions. The device features two output-enable ($\overline{nOE}$) inputs for easy cascading and two send/receive (nDIR) inputs for direction control. $\overline{nOE}$ controls the outputs so that the buses are effectively isolated. This device can be used as two 8-bit transceivers or one 16-bit transceiver. Inputs can be driven from either 3.3 V or 5 V devices. When disabled, up to 5.5 V can be applied to the outputs. These features allow the use of these devices in mixed 3.3 V and 5 V applications.

The 74LVCH16245A-Q100 bus hold on data inputs eliminates the need for external pull-up resistors to hold unused inputs.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from −40 °C to +85 °C and from −40 °C to +125 °C
- 5 V tolerant inputs/outputs for interfacing with 5 V logic
- Wide supply voltage range from 1.2 V to 3.6 V
- CMOS low power consumption
- MULTIBYTE flow-through standard pinout architecture
- Low inductance multiple power and ground pins for minimum noise and ground bounce
- Direct interface with TTL levels
- High-impedance when V_{CC} = 0 V
- All data inputs have bus hold (74LVCH16245A-Q100 only)
- Complies with JEDEC standard:
  - JESD8-7A (1.65 V to 1.95 V)
  - JESD8-5A (2.3 V to 2.7 V)
  - JESD8-C/JESD36 (2.7 V to 3.6 V)
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)

3. Ordering information

Table 1. Ordering information

Type number	Temperature range	Package		
		Name	Description	Version
74LVC16245ADGG-Q100	–40 °C to +125 °C	TSSOP48	plastic thin shrink small outline package; 48 leads; body width 6.1 mm	SOT362-1
74LVCH16245ADGG-Q100				
74LVC16245AEV-Q100	–40 °C to +125 °C	VFBGA56	plastic very thin fine-pitch ball grid array package; 56 balls; body 4.5 × 7 × 0.65 mm	SOT702-1
74LVCH16245AEV-Q100				

4. Functional diagram

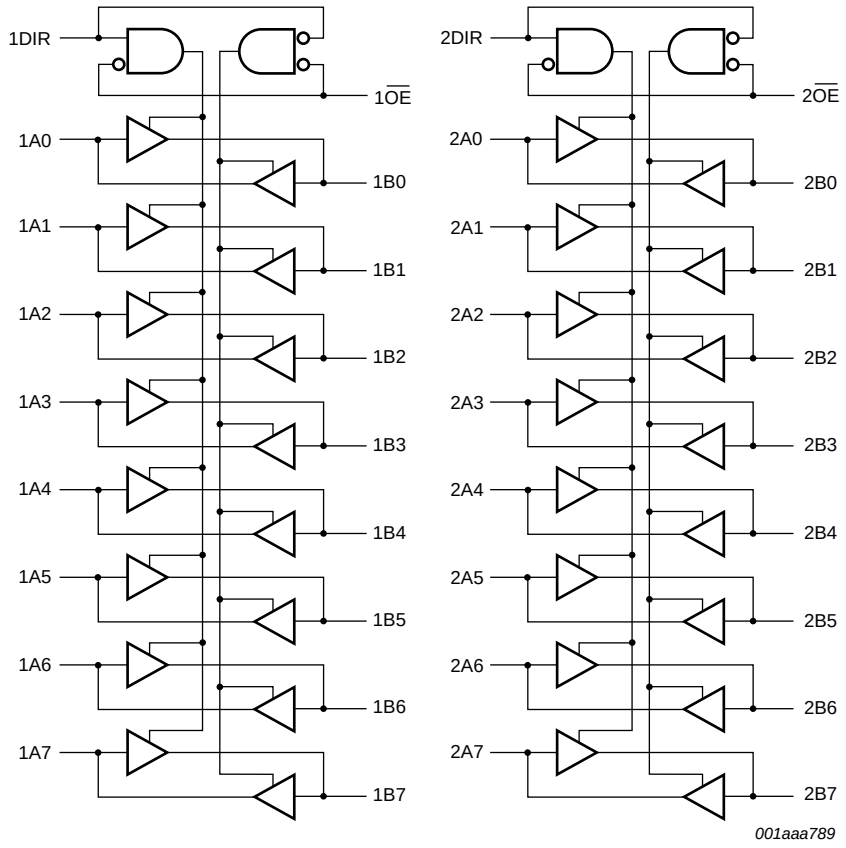


Fig 1. Logic symbol

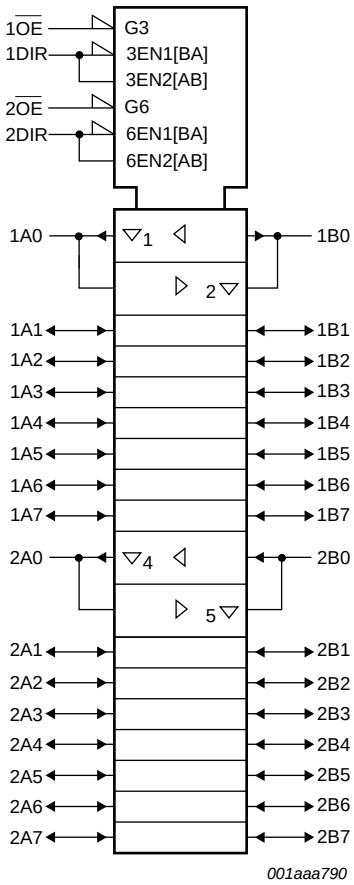


Fig 2. IEC logic symbol

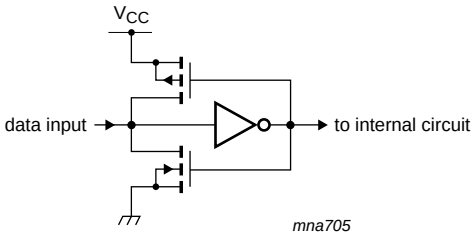


Fig 3. Bus hold circuit

5. Pinning information

5.1 Pinning

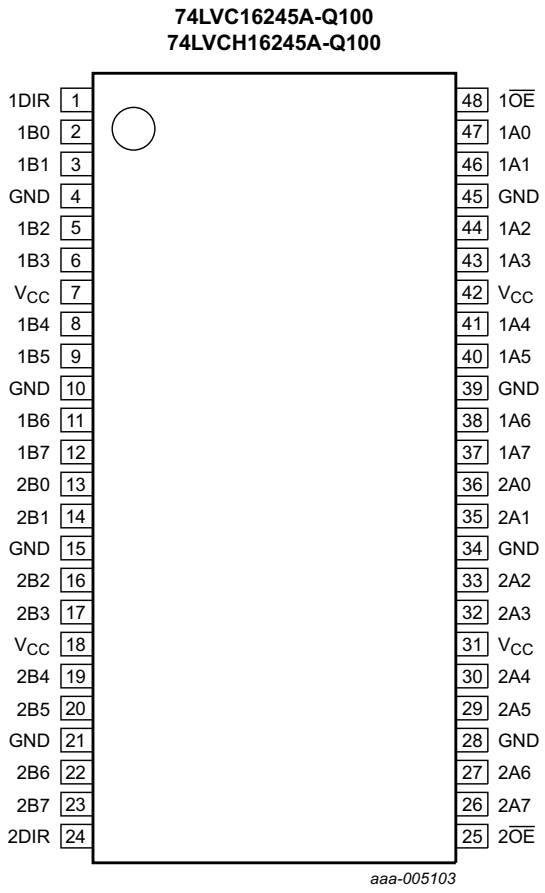


Fig 4. Pin configuration SOT362-1 (TSSOP48)

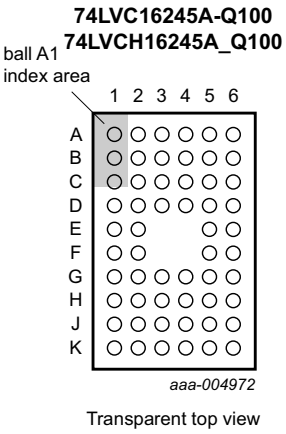


Fig 5. Pin configuration SOT702-1 (VFBGA56)

5.2 Pin description

Table 2. Pin description

Symbol	Pin		Description
	SOT362-1	SOT702-1	
1DIR, 2DIR	1, 24	A1, K1	direction control input
1B0 to 1B7	2, 3, 5, 6, 8, 9, 11, 12	B2, B1, C2, C1, D2, D1, E2, E1	data input/output
2B0 to 2B7	13, 14, 16, 17, 19, 20, 22, 23	F1, F2, G1, G2, H1, H2, J1, J2	data input/output
GND	4, 10, 15, 21, 28, 34, 39, 45	B3, B4, D3, D4, G3, G4, J3, J4	ground (0 V)
V_{CC}	7, 18, 31, 42	C3, C4, H3, H4	supply voltage
$1\overline{OE}$, $2\overline{OE}$	48, 25	A6, K6	output enable input (active LOW)
1A0 to 1A7	47, 46, 44, 43, 41, 40, 38, 37	B5, B6, C5, C6, D5, D6, E5, E6	data input/output
2A0 to 2A7	36, 35, 33, 32, 30, 29, 27, 26	F6, F5, G6, G5, H6, H5, J6, J5	data input/output
n.c.	-	A2, A3, A4, A5, K2, K3, K4, K5	not connected

6. Functional description

Table 3. Function table[1]

Inputs		Outputs	
$n\overline{OE}$	nDIR	nAn	nBn
L	L	nAn = nBn	inputs
L	H	inputs	nBn = nAn
H	X	Z	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+6.5	V
I_{IK}	input clamping current	$V_I < 0$ V		–50	-	mA
V_I	input voltage		[1]	–0.5	+6.5	V
I_{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V		-	±50	mA
V_O	output voltage	output HIGH or LOW	[2]	–0.5	V_{CC} + 0.5	V
		output 3-state	[2]	–0.5	+6.5	V
I_O	output current	V_O = 0 V to V_{CC}		-	±50	mA
I_{CC}	supply current			-	100	mA
I_{GND}	ground current			–100	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +125 °C;				
		TSSOP48 package	[3]	-	500	mW
		VFBGA56 package	[4]	-	1000	mW

[1] The minimum input voltage ratings may be exceeded if the input current ratings are observed.

[2] The output voltage ratings may be exceeded if the output current ratings are observed.

[3] Above 60 °C, the value of P_{tot} derates linearly with 5.5 mW/K.

[4] Above 70 °C, the value of P_{tot} derates linearly with 1.8 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.65	-	3.6	V
		functional	1.2	-	3.6	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage	output HIGH or LOW	0	-	V_{CC}	V
		output 3-state	0	-	5.5	V
T_{amb}	ambient temperature	in free air	–40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 1.2 V to 2.7 V	0	-	20	ns/V
		V_{CC} = 2.7 V to 3.6 V	0	-	10	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
V_{IH}	HIGH-level input voltage	V_{CC} = 1.2 V	1.08	-	-	1.08	-	V
		V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}	-	-	0.65 × V_{CC}	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 1.2 V	-	-	0.12	-	0.12	V
		V_{CC} = 1.65 V to 1.95 V	-	-	0.35 × V_{CC}	-	0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		V_{CC} = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = –100 μA; V_{CC} = 1.65 V to 3.6 V	V_{CC} – 0.2	-	-	V_{CC} – 0.3	-	V
		I_O = –4 mA; V_{CC} = 1.65 V	1.2	-	-	1.05	-	V
		I_O = –8 mA; V_{CC} = 2.3 V	1.8	-	-	1.65	-	V
		I_O = –12 mA; V_{CC} = 2.7 V	2.2	-	-	2.05	-	V
		I_O = –18 mA; V_{CC} = 3.0 V	2.4	-	-	2.25	-	V
		I_O = –24 mA; V_{CC} = 3.0 V	2.2	-	-	2.0	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = 100 μA; V_{CC} = 1.65 V to 3.6 V	-	-	0.2	-	0.3	V
		I_O = 4 mA; V_{CC} = 1.65 V	-	-	0.45	-	0.65	V
		I_O = 8 mA; V_{CC} = 2.3 V	-	-	0.6	-	0.8	V
		I_O = 12 mA; V_{CC} = 2.7 V	-	-	0.4	-	0.6	V
		I_O = 24 mA; V_{CC} = 3.0 V	-	-	0.55	-	0.8	V
I_I	input leakage current[2]	V_I = 5.5 V or GND; V_{CC} = 3.6 V	-	±0.1	±5	-	±20	μA
I_{OZ}	OFF-state output current[2][3]	V_I = V_{IH} or V_{IL}; V_O = 5.5 V or GND; V_{CC} = 3.6 V	-	±0.1	±5	-	±20	μA
I_{OFF}	power-off leakage current	V_I or V_O = 5.5 V; V_{CC} = 0.0 V	-	±0.1	±10	-	±20	μA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 3.6 V	-	0.1	20	-	80	μA
ΔI_{CC}	additional supply current	per input pin; V_I = V_{CC} – 0.6 V; I_O = 0 A; V_{CC} = 2.7 V to 3.6 V	-	5	500	-	5000	μA
C_I	input capacitance	V_{CC} = 0 V to 3.6 V; V_I = GND to V_{CC}	-	5.0	-	-	-	pF
$C_{I/O}$	input/output capacitance	V_{CC} = 0 V to 3.6 V; V_I = GND to V_{CC}	-	10	-	-	-	pF

Table 6. Static characteristics *...continued*

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
I_{BHL}	bus hold LOW current [4][5]	V_{CC} = 1.65; V_I = 0.58 V	10	-	-	10	-	µA
		V_{CC} = 2.3; V_I = 0.7 V	30	-	-	25	-	µA
		V_{CC} = 3.0; V_I = 0.8 V	75	-	-	60	-	µA
I_{BHH}	bus hold HIGH current [4][5]	V_{CC} = 1.65; V_I = 1.07 V	–10	-	-	–10	-	µA
		V_{CC} = 2.3; V_I = 1.7 V	–30	-	-	–25	-	µA
		V_{CC} = 3.0; V_I = 2.0 V	–75	-	-	–60	-	µA
I_{BHLO}	bus hold LOW overdrive current [4][6]	V_{CC} = 1.95 V	200	-	-	200	-	µA
		V_{CC} = 2.7 V	300	-	-	300	-	µA
		V_{CC} = 3.6 V	500	-	-	500	-	µA
I_{BHHO}	bus hold HIGH overdrive current [4][6]	V_{CC} = 1.95 V	–200	-	-	–200	-	µA
		V_{CC} = 2.7 V	–300	-	-	–300	-	µA
		V_{CC} = 3.6 V	–500	-	-	–500	-	µA

[1] All typical values are measured at V_{CC} = 3.3 V (unless stated otherwise) and T_{amb} = 25 °C.

[2] The bus hold circuit is switched off when $V_I > V_{CC}$ allowing 5.5 V on the input terminal.

[3] For I/O ports, the parameter I_{OZ} includes the input leakage current.

[4] Valid for data inputs of bus hold parts only (74LVCH16245A-Q100). Note that control inputs do not have a bus hold circuit.

[5] The specified sustaining current at the data input holds the input below the specified V_I level.

[6] The specified overdrive current at the data input forces the data input to the opposite input state.

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 8.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[2]	Max	Min	Max	
t_{pd}	propagation delay	nAn to nBn; nBn to nAn; see Figure 6 [1]						
		V_{CC} = 1.2 V	-	13.0	-	-	-	ns
		V_{CC} = 1.65 V to 1.95 V	1.5	5.2	12.2	1.5	13.8	ns
		V_{CC} = 2.3 V to 2.7 V	1.0	2.8	6.0	1.0	6.7	ns
		V_{CC} = 2.7 V	1.0	2.7	4.7	1.0	6.0	ns
		V_{CC} = 3.0 V to 3.6 V	1.0	2.4	4.5	1.0	6.0	ns
t_{en}	enable time	$\overline{nOE}$ to nAn, nBn; see Figure 7 [1]						
		V_{CC} = 1.2 V	-	15.0	-	-	-	ns
		V_{CC} = 1.65 V to 1.95 V	1.5	5.9	15.0	1.5	16.9	ns
		V_{CC} = 2.3 V to 2.7 V	1.0	3.3	7.9	1.0	8.8	ns
		V_{CC} = 2.7 V	1.5	3.5	6.7	1.5	8.5	ns
		V_{CC} = 3.0 V to 3.6 V	1.0	2.7	5.5	1.0	7.0	ns

Table 7. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 8.

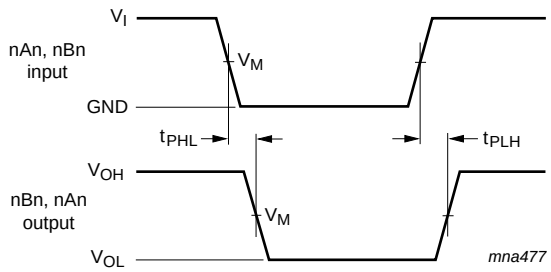
Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[2]	Max	Min	Max	
t_{dis}	disable time	$n\overline{OE}$ to nAn, nBn; see Figure 7 [1]						
		V_{CC} = 1.2 V	-	11.0	-	-	-	ns
		V_{CC} = 1.65 V to 1.95 V	1.0	4.9	13.1	1.0	14.7	ns
		V_{CC} = 2.3 V to 2.7 V	0.5	2.7	7.1	0.5	7.9	ns
		V_{CC} = 2.7 V	1.5	3.4	6.6	1.5	8.5	ns
		V_{CC} = 3.0 V to 3.6 V	1.5	3.3	5.6	1.5	7.0	ns
C_{PD}	power dissipation capacitance	per input; V_I = GND to V_{CC} [3]						
		V_{CC} = 1.65 V to 1.95 V	-	11.5	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V	-	15.2	-	-	-	pF
		V_{CC} = 3.0 V to 3.6 V	-	18.5	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL}.
t_{en} is the same as t_{PZL} and t_{PZH}.
t_{dis} is the same as t_{PLZ} and t_{PHZ}.

[2] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.2 V, 1.8 V, 2.5 V, 2.7 V and 3.3 V respectively.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz; f_o = output frequency in MHz
C_L = output load capacitance in pF
V_{CC} = supply voltage in Volts
N = number of inputs switching
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

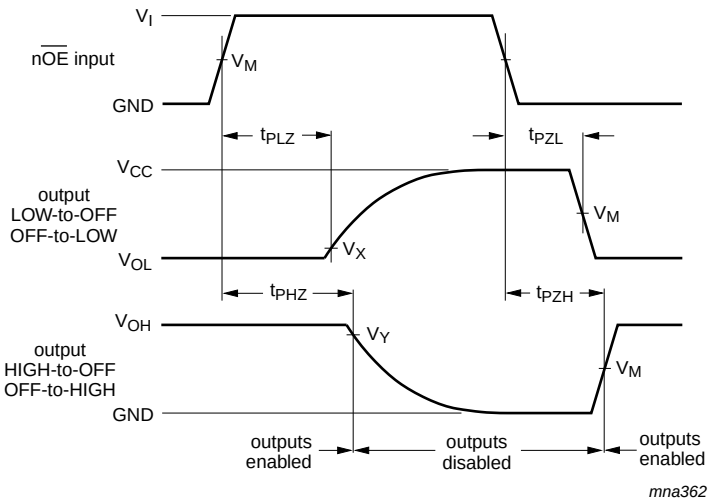
11. Waveforms



Measurement points are given in Table 8.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. The input (nAn, nBn) to output (nBn, nAn) propagation delays



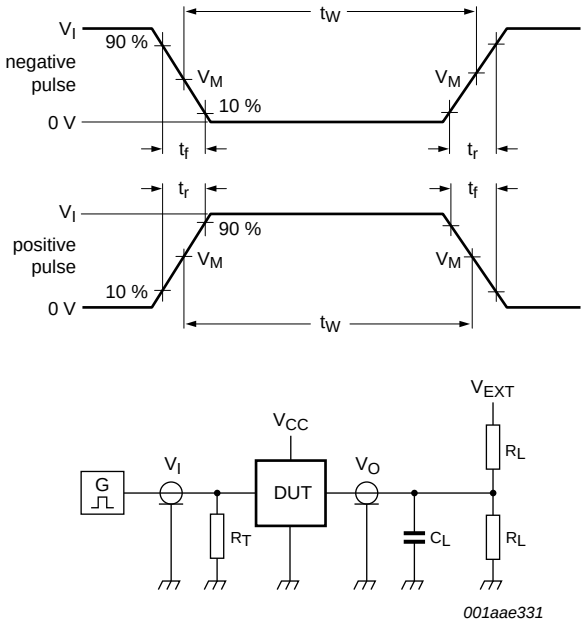
Measurement points are given in Table 8.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 7. 3-state enable and disable times

Table 8. Measurement points

Supply voltage	V_M	Input			
V_{CC}		V_I	$t_r = t_f$	V_X	V_Y
1.2 V	$0.5 \times V_{CC}$	V_{CC}	≤ 2.5 ns	V_{OL} + 0.15 V	V_{OH} − 0.15 V
1.65 V to 1.95 V	$0.5 \times V_{CC}$	V_{CC}	≤ 2.5 ns	V_{OL} + 0.15 V	V_{OH} − 0.15 V
2.3 V to 2.7 V	$0.5 \times V_{CC}$	V_{CC}	≤ 2.5 ns	V_{OL} + 0.15 V	V_{OH} − 0.15 V
2.7 V	1.5 V	2.7 V	≤ 2.5 ns	V_{OL} + 0.3 V	V_{OH} − 0.3 V
3.0 V to 3.6 V	1.5 V	2.7 V	≤ 2.5 ns	V_{OL} + 0.3 V	V_{OH} − 0.3 V



Test data is given in Table 9.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

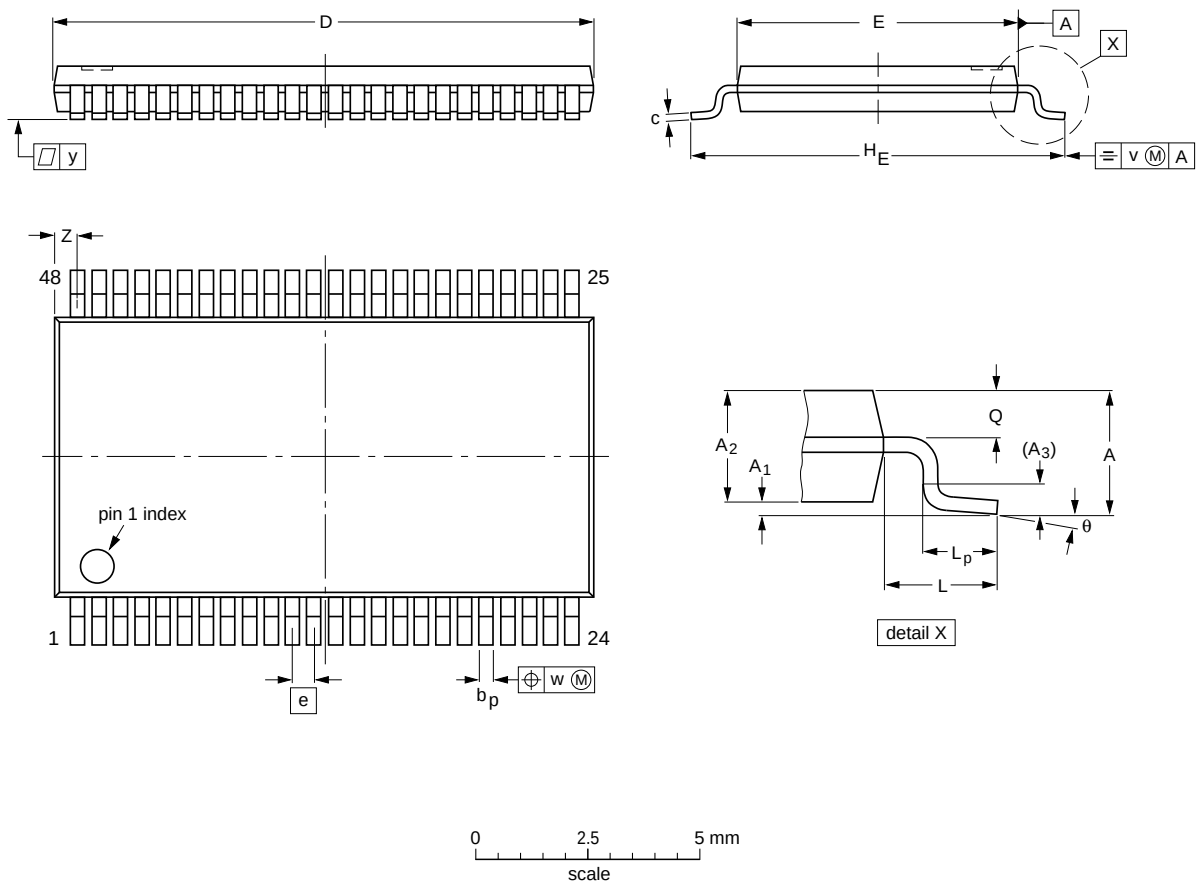
Fig 8. Test circuit for measuring switching times

Table 9. Test data

Supply voltage	Input		Load		V_{EXT}		
	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}	t_{PLZ}, t_{PZL}	t_{PHZ}, t_{PZH}
1.2 V	V_{CC}	≤ 2 ns	30 pF	1 kΩ	open	2 × V_{CC}	GND
1.65 V to 1.95 V	V_{CC}	≤ 2 ns	30 pF	1 kΩ	open	2 × V_{CC}	GND
2.3 V to 2.7 V	V_{CC}	≤ 2 ns	30 pF	500 Ω	open	2 × V_{CC}	GND
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	2 × V_{CC}	GND
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	2 × V_{CC}	GND

12. Package outline

TSSOP48: plastic thin shrink small outline package; 48 leads; body width 6.1 mm **SOT362-1**



DIMENSIONS (mm are the original dimensions).

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(2)}$	e	H_E	L	L_p	Q	v	w	y	Z	θ
mm	1.2	0.15 0.05	1.05 0.85	0.25	0.28 0.17	0.2 0.1	12.6 12.4	6.2 6.0	0.5	8.3 7.9	1	0.8 0.4	0.50 0.35	0.25	0.08	0.1	0.8 0.4	8^o 0^o

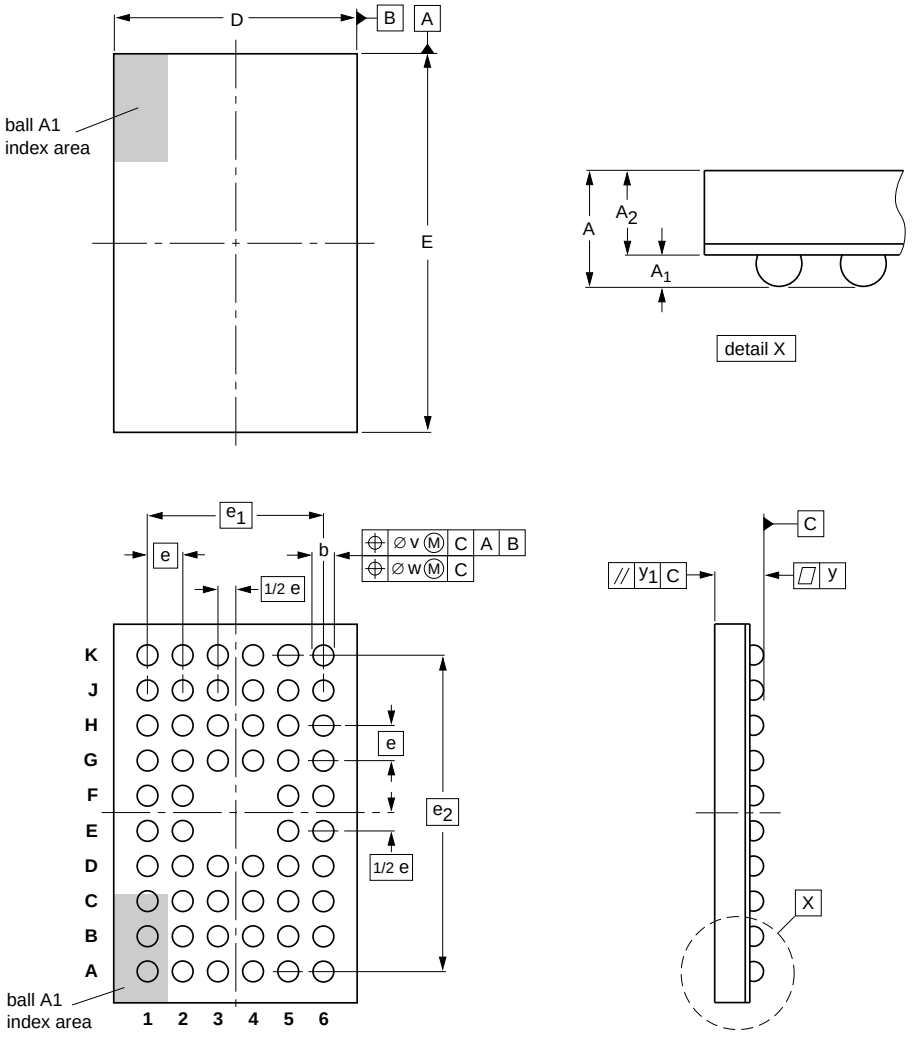
Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT362-1		MO-153				~~99-12-27~~ 03-02-19

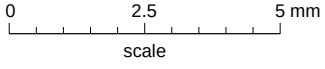
Fig 9. Package outline SOT362-1 (TSSOP48)

VFBGA56: plastic very thin fine-pitch ball grid array package; 56 balls; body 4.5 x 7 x 0.65 mm **SOT702-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	b	D	E	e	e_1	e_2	v	w	y	y_1
mm	1	0.3 0.2	0.7 0.6	0.45 0.35	4.6 4.4	7.1 6.9	0.65	3.25	5.85	0.15	0.08	0.08	0.1



OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT702-1		MO-225				~~02-08-08~~ 03-07-01

Fig 10. Package outline SOT702-1 (VFBGA56)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic
MIL	Military

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC_LVCH16245A_Q100 v.1	20121120	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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17. Contents

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